

MMBD2835, MMBD2836

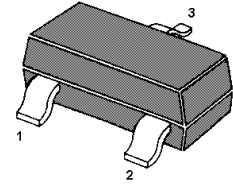
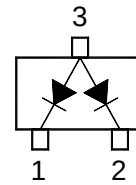
Silicon Epitaxial Planar Switching Diode

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

Applications

- Ultra high speed switching application



Marking Code: A1
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
MMBD2835		75	
Forward Current	I_F	100	mA
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V_F	-	1	V
at $I_F = 10\text{ mA}$			1	V
at $I_F = 50\text{ mA}$			1.2	V
Reverse Current	I_R	-	100	nA
at $V_R = 30\text{ V}$			100	
at $V_R = 50\text{ V}$	MMBD2835	-	-	-
Reverse Breakdown Voltage	$V_{(BR)R}$	35	-	V
at $I_R = 100\text{ }\mu\text{A}$		75	-	
Diode Capacitance	C_T	-	4	pF
at $V_R = 0$, $f = 1\text{ MHz}$			4	
Reverse Recovery Time	t_{rr}	-	4	ns
at $I_F = I_R = 10\text{ mA}$, $I_{R(REC)} = 1\text{ mA}$			4	

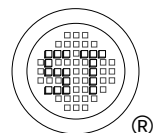


FIGURE 1. RECOVERY TIME EQUIVALENT TEST CIRCUIT

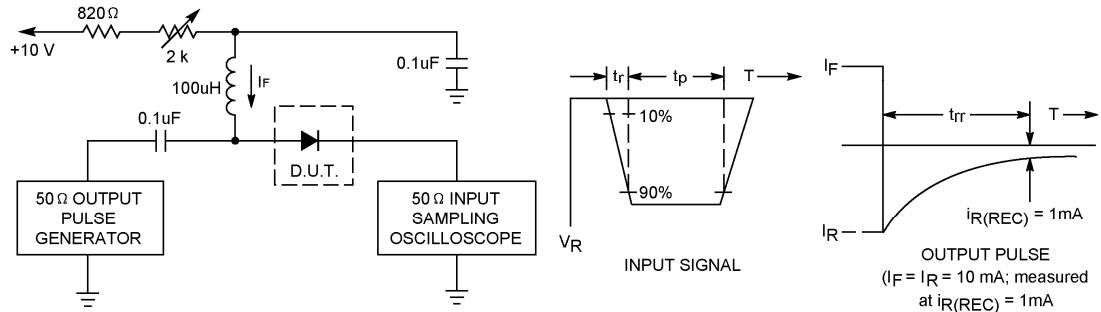


FIGURE 2. FORWARD VOLTAGE

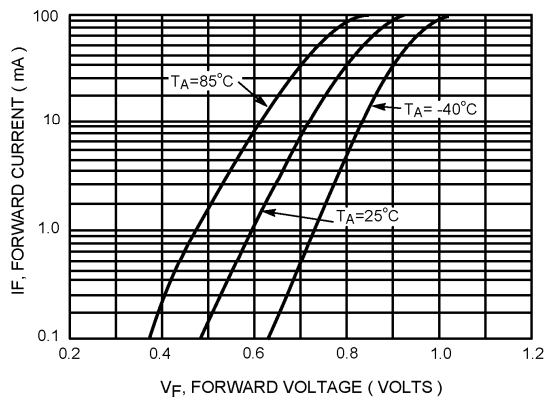


FIGURE 3. LEAKAGE CURRENT

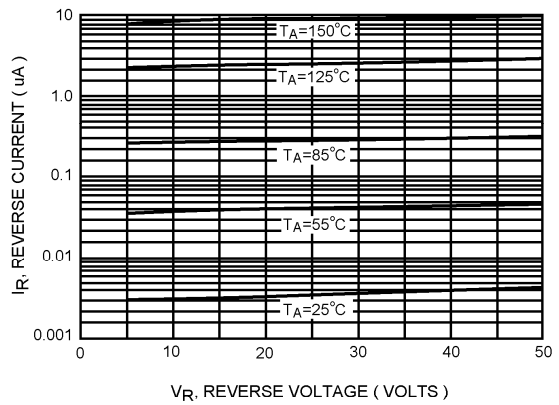


FIGURE 4. CAPACITANCE

